L Number	Hits	Search Text	DB	Time stamp
23	171	p-type adj polysilicon near4 gate	USPAT;	2002/04/06 13:46
			US-PGPUB	
24 ,	279	p-type adj polysilicon same gate	USPAT;	2002/04/06 13:46
			US-PGPUB	
25	108	(p-type adj polysilicon same gate) not (p-type adj polysilicon	USPAT;	2002/04/06 13:46
		near4 gate)	US-PGPUB	
26	67	p-type adj polysilicon near4 gate	EPO; JPO;	2002/04/06 15:46
			DERWENT;	
			IBM TDB	
27	11	YAMAGUCHI.in. and SHUSAKU.in.	USPAT;	2002/04/06 15:21
			US-PGPUB	
28	71800	YAMAGUCHI.in. SHUSAKU.in.	EPO; JPO;	2002/04/06 15:21
		•	DERWENT;	
			IBM_TDB	
29	0	jp-09036318-\$.did.	USPAT;	2002/04/06 15:22
			US-PGPUB	
-	53807	drain near2 source	USPAT;	2002/04/05 15:04
			US-PGPUB	
-	1033	(drain near2 source) near2 ground	USPAT;	2002/04/05 15:04
			US-PGPUB	
- !	851	((drain near2 source) near2 ground) same gate	USPAT;	2002/04/05 15:04
			US-PGPUB	
-	186	((drain near2 source) near2 ground) same (gate near2	USPAT;	2002/04/05 15:21
		(supply voltage))	US-PGPUB	
-	174	capacitor adj connected adj transistor	USPAT;	2002/04/05 15:21
			US-PGPUB	
-	19	(capacitor adj connected adj transistor) same ground	USPAT;	2002/04/05 16:32
			US-PGPUB	
-	17	7.clm.	USPAT;	2002/04/05 16:33
			US-PGPUB	
-	171	p-type adj polysilicon near4 gate	USPAT;	2002/04/06 14:19
			US-PGPUB	
-	1	("6000843").PN.	USPAT;	2002/04/05 17:04
		•	US-PGPUB	